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INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

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Sheet 1 of 8

Complete if Known

Application Number	09/938,672
Filing Date	August 27, 2001
First Named Inventor	John T. Moore
Art Unit	2152
Examiner Name	T. Washington
Attorney Docket Number	M4065.0475/P475

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
LDP	AA	6,388,324	05/14/2002	Kozicki et al.	RECEIVED NOV 06 2002 Technology Center 2100
	AB	US 2002/0000666	01/03/2002	Kozicki et al.	
	AC	5,500,532	03/19/1996	Kozicki et al.	
	AD	6,418,049	07/09/2002	Kozicki et al.	
	AE	5,751,012	05/12/1998	Wolstenholme et al.	
	AF	5,789,277	08/04/1998	Zahorik et al.	
LDP	AG	6,348,365	02/19/2202	Moore et al.	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
LDP	BA	WO 02/21542	03/14/2002	Kozicki et al.		
LDP	BB	WO 00/48196	08/17/2000	Kozicki et al.		
LDP	BC	WO 97/48032	12/18/1997	Kozicki et al.		
LDP	BD	WO 99/28914	06/10/1999	Kozicki et al.		

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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Substitute for form 1449B/PTO			Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Application Number	09/938,672	
			Filing Date	August 27, 2001	
			First Named Inventor	John T. Moore	
			Group Art Unit	2152	
			Examiner Name	T. Washington	
			Attorney Docket Number	M4065.0475/P-475	
Sheet	2	of	8	RECEIVED NOV 06 2002 Technology Center 2100	

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T ²
MDP	CA	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge ₅ As ₃₈ Te ₅₇ chalcogenide glass, Vacuum 59 (2000) 845-853.		
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	CD	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se ₇₅ Ge ₂₅ -xSbx, Appl. Phys. A 55 (1992) 167-169.		
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	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.		
	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810		
	CL	Baranovskii, S.D.; Cordes, H., On the conduction mechanism in ionic glasses, J. Chem. Phys. 111 (1999) 7546-7557.		
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	CS	Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin solid films 131 (1985) L61-L64.		
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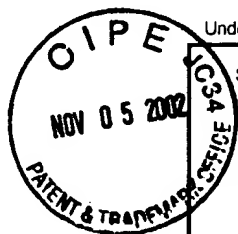
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 Sheet **3** of **8**

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LD		Glasses, Asian Journal of Physics (2000) 9, 709-72.	
	CX	Boolchand, P.; Bresser, W.J., Mobile silver ions and glass formation in solid electrolytes, Nature 410 (2001) 1070-1073.	
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	CP1	Dalven, R.; Gill, R., Electrical properties of beta-Ag ₂ Te and beta-Ag ₂ Se from 4.2 to 300K, J. Appl. Phys. 38 (1967) 753-756.	
	CQ1	Davis, E.A., Semiconductors without form, Search 1 (1970) 152-155.	
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Sheet 4 of 8

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First Named Inventor	John T. Moore
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Attorney Docket Number	M4065.0475/P475

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First Named Inventor	John T. Moore	
Group Art Unit	2152	
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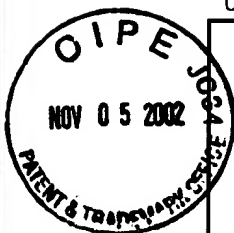
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Sheet	6	of	8
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CQ3	Kolobov, A.V., On the origin of p-type conductivity in amorphous chalcogenides, J. Non-Cryst. Solids 198-200 (1996) 728-731.
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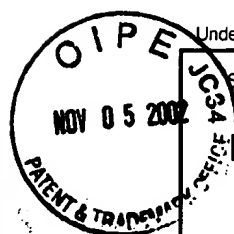
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Sheet	7	of	8	Application Number	09/938,672
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Complete if Known

Application Number	09/938,672
Filing Date	August 27, 2001
First Named Inventor	John T. Moore
Group Art Unit	2152
Examiner Name	T. Washington
Attorney Docket Number	M4065.0475/P475

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STATEMENT BY APPLICANT

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Sheet	8	of	8	Application Number	09/938,672	RECEIVED
				Filing Date	August 27, 2001	
				First Named Inventor	John T. Moore	NOV 05 2002
				Group Art Unit	2152	Technology Center 2100
				Examiner Name	T. Washington	
				Attorney Docket Number	M4065.0475/P475	

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Examiner Signature	<i>Marcel S. Vignard</i>	Date Considered	4/22/2003
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				Application Number	09/938,672
				Filing Date	August 27, 2001
				First Named Inventor	John Moore
				Art Unit	2152
				Examiner Name	T. Washington
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U.S. PATENT DOCUMENTS					
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		Number-Kind Code ² (if known)			
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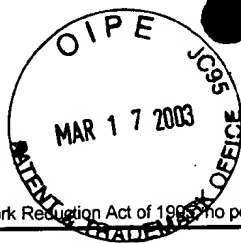
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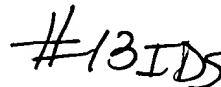
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			Filing Date	February 13, 2003	
			First Named Inventor	John Moore	
			Art Unit	2151	
			Examiner Name	Not Yet Assigned	
Sheet	1	of	4	Attorney Docket Number	M4065.0475/P475-A

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LSP	BA	JP 56126916	10/1981	Akira et al.		
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	CE	Holmquist et al., <i>Reaction and Diffusion in Silver-Arsenic Chalcogenide Glass Systems</i> , 62 J. AMER. CERAM. SOC., No. 3-4, pp. 183-188 (March-April 1979).	
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	CN	Owen et al., <i>Metal-Chalcogenide Photoresists for High Resolution Lithography and Sub-Micron Structures</i> , NANOSTRUCTURE PHYSICS AND FABRICATION, pp. 447-451 (M. Reed ed. 1989).	
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Examiner Signature	<i>Monica D. Rigaud-Crespo</i>	Date Considered	4/22/2003
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>			Complete if Known		
			Application Number	09/938,672	
			Filing Date	August 27, 2001	
			First Named Inventor	John Moore	
			Art Unit	2151	
			Examiner Name	T. Washington	
Sheet	1	of	4	Attorney Docket Number	M4065.0475/P475

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Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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				Application Number	09/938,672
				Filing Date	August 27, 2001
				First Named Inventor	John Moore
				Art Unit	2151
				Examiner Name	T. Washington
Sheet	2	of	4	Attorney Docket Number	M4065.0475/P475

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Sheet	3	of	4

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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
MS	BA	JP 56126916	10/1981	Akira et al.		
	BB					

Examiner Signature	<i>Marcel D. Liguori-Brief</i>	Date Considered	8/18/2003
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¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	09/938,672
				Filing Date	August 27, 2001
				First Named Inventor	John Moore
				Group Art Unit	2151
				Examiner Name	T. Washington
				Attorney Docket Number	M4065.0475/P475
Sheet	4	M4	4		

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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	CD	Hirose et al., <i>High Speed Memory Behavior and Reliability of an Amorphous As₂S₃ Film Doped Ag</i> , PHYS. STAT. SOL. (a) 61, pp. 87-90 (1980).	
	CE	Holmquist et al., <i>Reaction and Diffusion in Silver-Arsenic Chalcogenide Glass Systems</i> , 62 J. AMER. CERAM. SOC., No. 3-4, pp. 183-188 (March-April 1979).	
	CF	Huggett et al., <i>Development of silver sensitized germanium selenide photoresist by reactive sputter etching in SF₆</i> , 42 APPL. PHYS. LETT., No. 7, pp. 592-594 (April 1983).	
	CG	Kawaguchi et al., <i>Mechanism of photosurface deposition</i> , 164-166 J. NON-CRYST. SOLIDS, pp. 1231-1234 (1993).	
	CH	Kolobov and Elliott, Photodoping of Amorphous Chalcogenides by Metals, <i>Advances in Physics</i> , Vol. 40, No 5, 625-684 (1991).	
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AMP	CO	Shimizu et al., <i>The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses</i> , 46 B. CHEM SOC. JAPAN, No. 12, pp. 3662-3365 (1973).	
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